

Schottky Rectifier

$I_F = 10\text{ A}$
 $V_R = 45\text{ V}$
 $V_F = 0.42\text{ V}$

Description/ Features

This low cost Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150°C junction temperature. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.

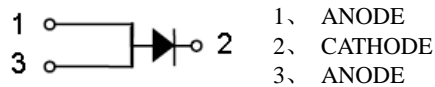
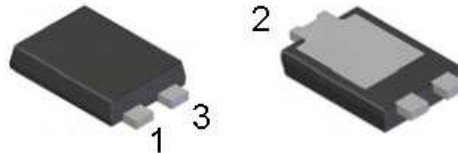
- 150°C T_j operation
- Low Power Loss, High Efficiency
- Low forward voltage drop
- High surge capacity
- Lead Free Finish/ROHS Compliant(Note 1)

Major Ratings and Characteristics

Characteristics	Values	Units
I _F	10	A
I _{FSM}	150	A
V _R	45	V
V _F	0.42	V
T _J	150	°C
T storage	-55 ~150	°C

Case Styles

TO-277



Ordering Information

Part Number	Package	Packaging
MV10T45	TO-277	Tape & Reel

MV10T45

Electrical Characteristics(T_{amb}=25°C)

Characteristic	Symbol	Value		Unit
Peak Repetitive Reverse Voltage	V _{RRM}	45		V
Working Peak Reverse Voltage	V _{RWM}			
DC Blocking Voltage	V _R			
Average Rectifier Output Current	I _F	10		A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase,60Hz)	I _{FSM}	150		A
Maximum Instantaneous Forward Voltage @ I _F =2A, T _c =25°C @ I _F =2A, T _c =125°C @ I _F =5A, T _c =25°C @ I _F =5A, T _c =125°C @ I _F =10A, T _c =25°C @ I _F =10A, T _c =125°C	V _F	TYP. 0.33 0.26 0.38 0.32 0.42 0.38	MAX. 0.36 0.31 0.41 0.37 0.46 0.42	V
Peak Reverse Current @T _a =25°C at Rated DC Blocking Voltage @T _a =125°C	I _R	0.3 20		mA
Typical Junction Capacitance	C _J	600		pF
Maximum Operating Junction Temperature	T _j	150		°C
Storage Temperature	T _{STG}	-55~150		
Maximum Thermal Resistance (Note 2)	θ _{JA}	31		°C/W
	θ _{JM}	4		°C/W

Notes:1.High Temperature Solder Exemption Applied, See EU Directive Annex 7.

2. θ_{JM} :Junction to cathode terminal.The device mounted on 1in² FR4 board with 2OZ. copper.



Characteristics Curve

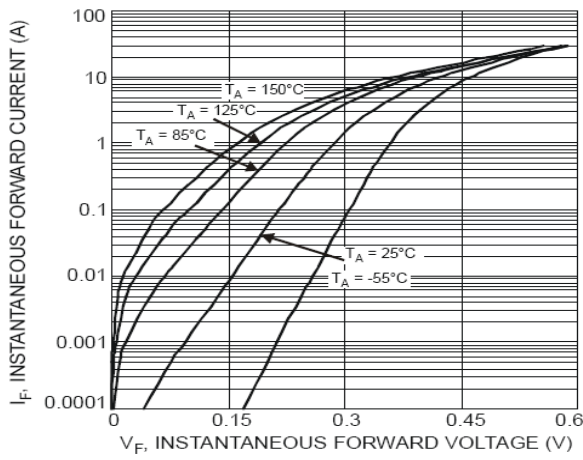


Figure 1. Typical Forward Voltage Per Diode

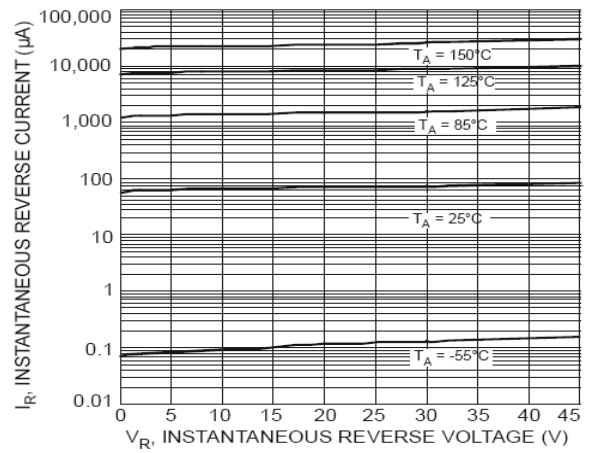


Figure 2. Typical Reverse Current Per Diode

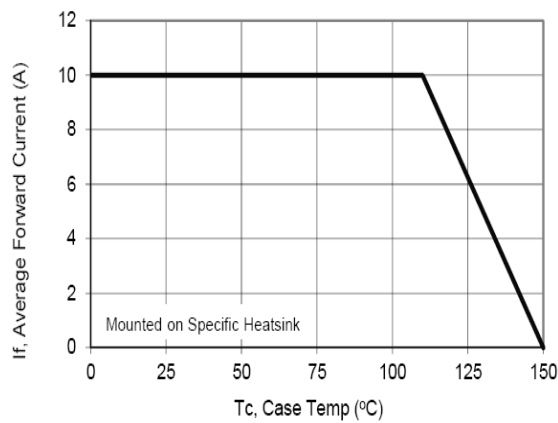


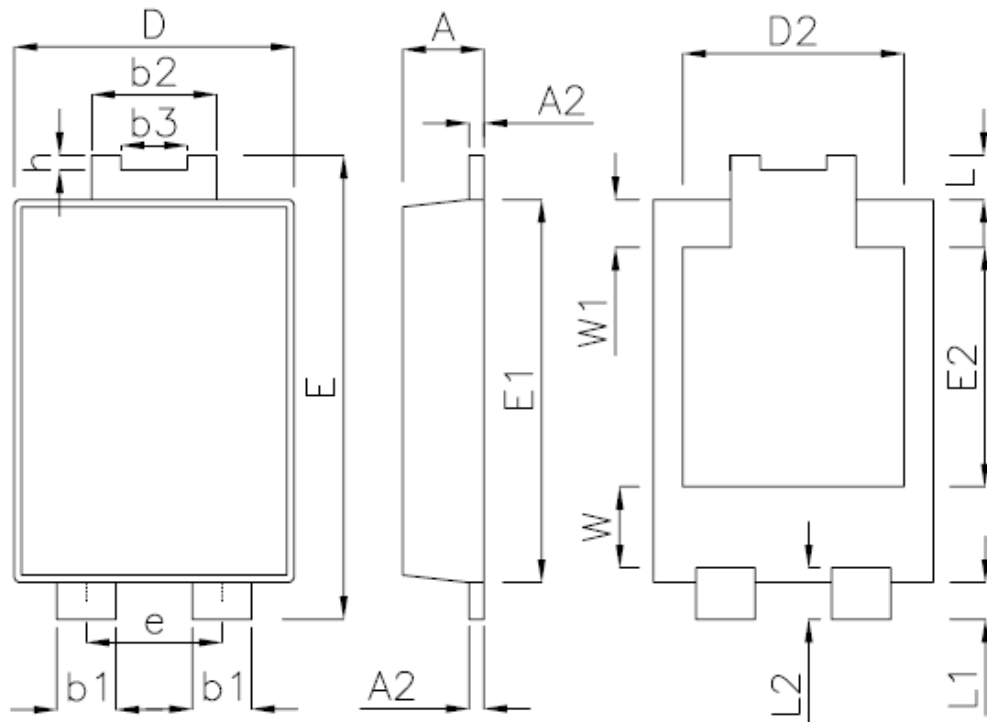
Figure 3. Average Forward Current vs Case Temperature Per Diode

MV10T45

TO-277 Mechanical Data

UNIT.: mm

SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	1.05	1.20	e	1.65	1.95
A2	0.30	0.45	E1	5.30	5.80
b1	0.80	1.00	E2	3.10	3.60
b2	1.70	1.90	L	0.50	0.70
b3	0.70	0.90	L1	0.50	0.70
L2	0.80	1.10	h	0.10	0.20
D	3.85	4.30	D2	2.90	3.30
W	1.10	1.40	E	6.30	6.60
W1	0.30	0.50			



Data and specifications subject to change without notice.

This product has been designed and qualified for Industrial Level and Lead-Free.

Qualification Standards can be found on GS's Web site.

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